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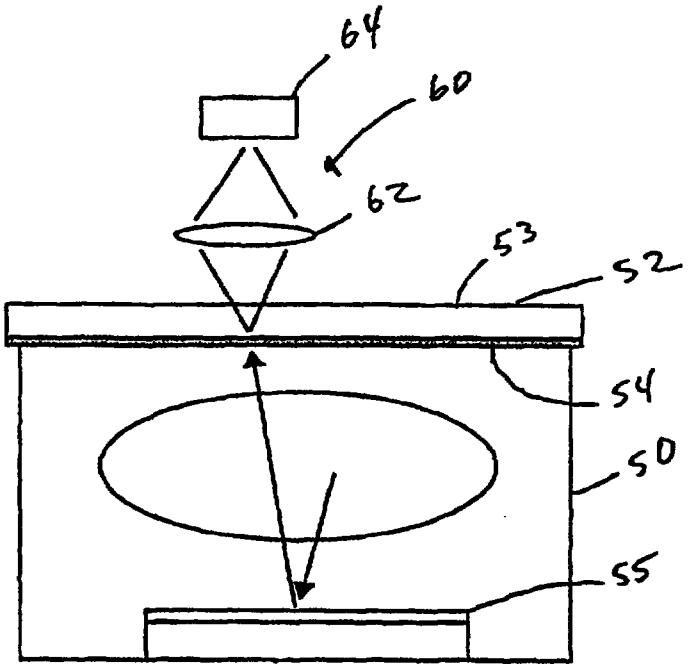
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(54) Title: INTERFEROMETRIC METHOD FOR ENDPOINTING PLASMA ETCH PROCESSES



(57) Abstract: A method for monitoring a device fabrication process. The method includes etching into a wafer disposed inside a chamber and detecting the intensity of a portion of a light reflected from a surface of the wafer and further scattered at a scattering inside surface of the chamber.